

# isc N-Channel MOSFET Transistor

## **SMK0990CI**

#### FEATURES

- · New revolutionary high voltage technology
- With TO-3PN package
- Drain-Source breakdown voltage:BV<sub>DSS</sub>=900V(Min.)
- Low drain-source On resistance:  $R_{DS}(on)=1.4\Omega$  (Max.)
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### APPLICATIONS

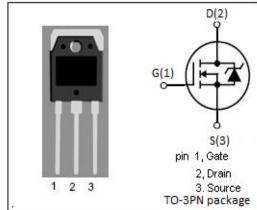
· Switching applications

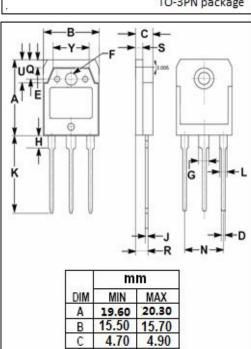


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|--|--|----------|--------------|--|--|
| SYMBOL   | PARAMETER                                    | VALUE    | UNIT         |  |  |
| V <sub>DSS</sub>                                     | Drain-Source Voltage                         | 900      | V            |  |  |
| V <sub>GSS</sub>                                     | Gate-Source Voltage                          | ±30      | V            |  |  |
| I <sub>D</sub>                                       | Drain Current-Continuous@Tc=25°C<br>Tc=100°C | 9<br>5.7 | А            |  |  |
| I <sub>DM</sub>                                      | Drain Current-Single Pulsed                  | 36       | А            |  |  |
| P <sub>D</sub>                                       | Total Dissipation                            | 130      | W            |  |  |
| T <sub>j</sub>                                       | Operating Junction Temperature               | -55~150  | $^{\circ}$   |  |  |
| T <sub>stg</sub>                                     | Storage Temperature                          | -55~150  | $^{\circ}$ C |  |  |

### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |      | UNIT |  |
|-----------|---------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 0.96 | °C/W |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 40   | °C/W |  |





| DIM | MIN   | MAX   |
|-----|-------|-------|
| Α   | 19.60 | 20.30 |
| В   | 15.50 | 15.70 |
| C   | 4.70  | 4.90  |
| D   | 0.90  | 1.10  |
| E   | 1.90  | 2.10  |
| F   | 3.40  | 3.60  |
| G   | 2.90  | 3.20  |
| Н   | 3.20  | 3.40  |
| J   | 0.595 | 0.605 |
| K   | 19.80 | 20.70 |
| L   | 1.90  | 2.20  |
| N   | 10.89 | 10.91 |
| Q   | 4.90  | 5.10  |
| R   | 3.35  | 3.45  |
| S   | 1.995 | 2.100 |
| U   | 5.90  | 6.20  |
| Υ   | 9.90  | 10.10 |



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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | ТҮР  | MAX      | UNIT       |
|---------------------|--------------------------------|---|-----|------|----------|------------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA  | 900 |      |          | V          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =±30V; I <sub>D</sub> =0.25mA   | 3   |      | 5        | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =4.5A   |     | 1.12 | 1.4      | Ω          |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V  |     |      | ±0.1     | μ <b>А</b> |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = 900V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C<br>T <sub>J</sub> =125°C |     |      | 1<br>100 | μА         |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =9.5A, V <sub>GS</sub> = 0 V  |     |      | 1.4      | V          |

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